

IDS 12/12/2003

Form PTO-1449 - U.S. DEPARTMENT OF COMMERCE (REV. 7-80) PATENT AND TRADEMARK OFFICE				Atty. Docket No. YOR919970121US2 (16323A)		Serial N. <u>10/735,167</u> <del>10/735,167</del>	
<b>LIST OF PRIOR ART CITED BY APPLICANT</b>  (Use several sheets if necessary)				Applicant Frank Cardone, et al.			
				Filing Date Herewith		Group <u>2822</u> <del>2822</del>	

  

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL*	AA	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (if appropriate)
<i>KBD</i>          ↓	AA	5,316,958	5/31/1994	Meyerson			
	AB	5,628,834	5/13/1997	Copel et al.			
		5,047,365	9/10/1991	Kawanaka et al.			
		5,241,197	8/31/1993	Murakami et al.			
		5,298,452	3/29/1994	Meyerson			
		5,089,428	2/18/1992	Verret et al.			
		5,616,515	4/1/1997	Okuno			
		5,607,511	3/4/1997	Meyerson			
		5,181,964	1/20/1993	Meyerson			
		5,227,644	7/1993	Ueno			

  

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL*	AA	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
<i>KBD</i>   ↓		494,395	7/15/1992	Europe				
		2-288328	11/28/1998	Japan				
		63-168021	7/12/1988	Japan				
	↓		6,061,489	3/4/1994	Japan			

  

OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)	
<i>KBD</i>  ↓	Sheldon P. et al. (1986) "Growth, Nucleation, and Electrical properties of Molecular Beam Epitaxially grown, As-doped Ge on Si Substrates" J. Vac. Sci & Tech. A, Vol. 4, No. 3, pt. 1, pgs. 889-893;
↓	Ismail K, et al (1992) "High Transconductance n-type Si/SiGe Modulation-Doped Field-Effect Transistors" IEEE Electron Device Letters, Vol. 13, No. 5, pgs. 229-231; and
↓	Ismail K, et al. (1991) High Electron Mobility in Modulation-Doped Si/SiGe" Applied Physics Letters, Vol. 58, No. 19, pgs. 2117-2119.

  

EXAMINER <i>John H. Phang</i>	DATE CONSIDERED <u>6/25/2005</u>
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\* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.